

IN THE CLAIMS

Please substitute the following amended claims for corresponding claims previously presented. A copy of the amended claims showing current revisions is attached.

3. A method according to Claim 1 characterised in that the mechanical shadow mask comprises a silicon wafer (92) having etched apertures (23) and an oxide film coating (91) upon which deposition does not occur at temperatures used for growth by chemical beam epitaxy.

4. A method according to claim 1 characterised in that the semiconductor device is a device (31, 100) for guiding radiation.